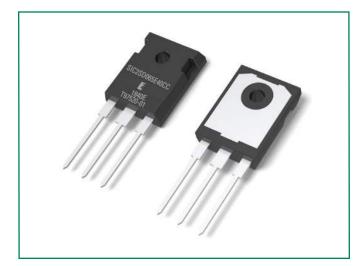
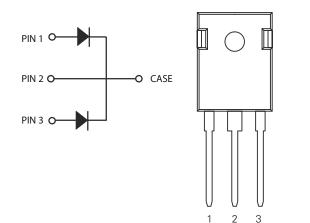
LSIC2SD065E40CCA 650 V, 40 A SiC Schottky Barrier Diode 🛛 🖨 AUTOMOTIVE GRADE HF Rohs 🐼



Circuit Diagram TO-247-3L



Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C. maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations
- Uninterruptible power supplies

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

Maximum Ratings

Maximum natings				
Characteristics	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	-	650	V
DC Blocking Voltage	V _R	T _J = 25 °C	650	V
Continuous Forward Current (Per Leg/Component)	I _F	$T_c = 25 \text{ °C}$	45 / 90	- A
		T _c = 135 °C	20 / 40	
Non-Repetitive Forward Surge Current (Per Leg)	I _{FSM}	$T_c = 25 \text{ °C}, T_p = 10 \text{ ms}, \text{ Half sine pulse}$	90	А
Power Dissipation (Per Leg/Component)	P _{Tot}	T _c = 25 °C	135 / 270	W
		T _c = 110 °C	60 / 120	
Operating Junction Temperature	TJ	-	-55 to 175	°C
Storage Temperature	T _{stg}	-	-55 to 150	°C
Soldering Temperature	T _{sold}	-	260	°C

Electrical Characteristics (T₁ = 25 °C unless otherwise specified)

Characteristics Symbol			Value			
	Conditions	Min.	Тур.	Max.	Unit	
Forward Voltage V _F -	I _F = 20 A, Τ _J = 25 °C	-	1.5	1.8	V	
	I _F = 20 A, T _J = 175 °C	-	1.85	-	V	
Reverse Current I _R	V _R = 650 V, T _J = 25 °C	-	<1	50		
	$V_{_{ m R}} = 650$ V, $T_{_{ m J}} = 175~^{\circ}{ m C}$	-	60	-	μA	
Total Capacitance C	$V_{R} = 1 V$, f = 1 MHz	-	960	-		
	V _R = 200 V, f = 1 MHz	-	120	-	pF	
	V _R = 400 V, f = 1 MHz	-	86	-		
Total Capacitive Charge	Q _c	$V_{R} = 400 \text{ V}, Q_{C} = \int_{0}^{V_{R}} C(V) dV$	-	63	-	nC

Thermal Characteristics

Figure 1: Typical Foward Characteristics

Characteristics	Symbol	Value	Unit
Thermal Resistance (Per Leg/Component)	R _{aic}	1.10 / 0.55	°C/W

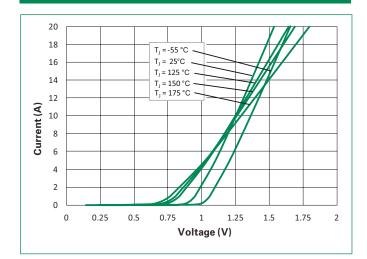


Figure 2: Typical Reverse Characteristics

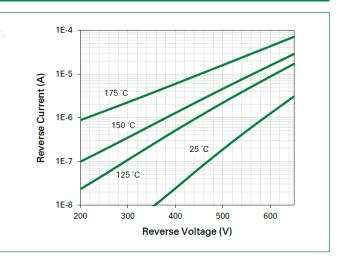


Figure 3: Power Derating

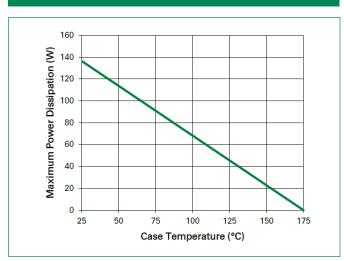
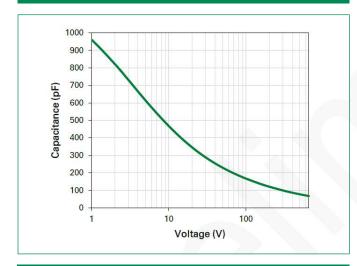
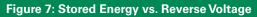


Figure 5: Capacitance vs. Reverse Voltage





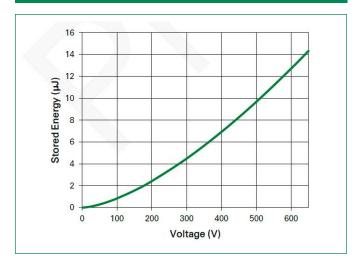


Figure 4: Current Derating

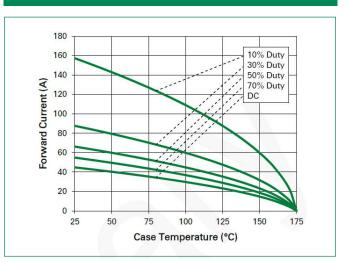


Figure 6: Capacitive Charge vs. Reverse Voltage

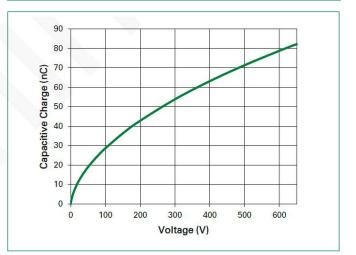
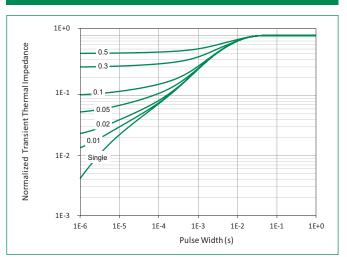


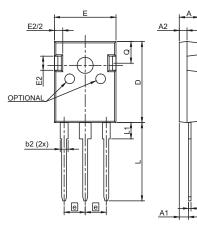
Figure 8: Transient Thermal Impedance

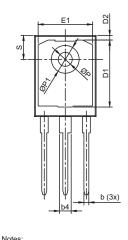


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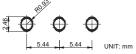
GEN2 SiC Schottky Diode LSIC2SD065E40CCA, 650 V, 40 A, TO-247-3L

Package Dimensions TO-247-3L





Recommended Hole Pattern Layout



Notes.
1. Dimensions are in millimeters
2. Dimension D, E do not include mold flash. Mold flash
shall not exceed 0.127 mm per side. These measured

at the outermost extreme of plastic body. 3.øP to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 0.154"

Symbol	Millimeters			
Symbol	Min	Nom	Max	
А	4.80	5.03	5.20	
A1	2.25	2.38	2.54	
A2	1.85	1.98	2.11	
b	0.99	-	1.40	
b2	1.65	-	2.39	
b4	2.59	-	3.43	
С	0.38	0.64	0.89	
D	20.80	20.96	21.34	
D1	13.50	-	-	
D2	0.51	1.19	1.35	
е		5.44 BSC		
E	15.75	15.90	16.13	
E1	13.06	14.02	14.15	
E2	4.19	4.32	4.83	
L	19.81	20.19	20.57	
L1	3.81	4.19	4.45	
øP	3.55	3.61	3.66	
øP1	7.06	7.19	7.32	
Q	5.49	5.61	6.20	
S	6.05	6.17	6.30	

SIC = SIC2SD065E40CC SD = U SD = YWWX E = ZZZZZZZZZZZ 40 = CC = Y Y = Y

WW

Х

Part Numbering and Marking System

- = SiC
- = Gen2
- = Schottky Diode
- = Voltage Rating (650 V) = TO-247-3L
- = Current Rating (40 A)
- = Common Cathode
- = Year
- = Week
- = Special Code
- ZZZZZZ-ZZ = Lot Number

Packing Options				
Part Number	Marking	Packing Mode	M.O.Q	
LSIC2SD065E40CCA	SIC2SD065E40CC	Tube (30pcs)	450	

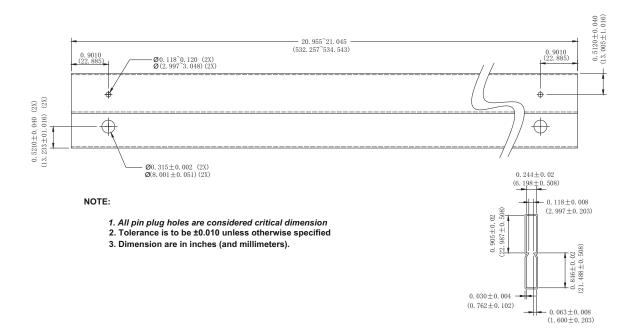
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GEN2 SiC Schottky Diode LSIC2SD065E40CCA, 650 V, 40 A, TO-247-3L

Packing Specification TO-247-3L



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